March 2015

FDD6680AS

30V N-Channel PowerTrench® SyncFET™

General Description

The FDD6680AS is designed to replace a single MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low $R_{DS(ON)}$ and low gate charge. The FDD6680AS includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology. The performance of the FDD6680AS as the low-side switch in a synchronous rectifier is indistinguishable from the performance of the FDD6680A in parallel with a Schottky diode.

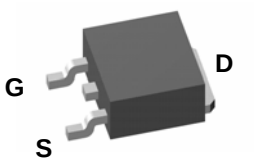
Applications

- DC/DC converter
- Low side notebook

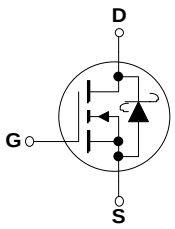
Features

- 55 A, 30 V $R_{DS(ON)}$ max= 10.5 mΩ @ V_{GS} = 10 V
  $R_{DS(ON)}$ max= 13.0 mΩ @ V_{GS} = 4.5 V
- Includes SyncFET Schottky body diode
- Low gate charge (21nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability

.



TO-252



Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current – Continuous	(Note 3)	55	A
	– Pulsed	(Note 1a)	100	
P_D	Power Dissipation	(Note 1)	60	W
		(Note 1a)	3.1	
		(Note 1b)	1.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	2.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6680AS	FDD6680AS	13''	16mm	2500 units

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 2)						
W_{DSS}	Drain-Source Avalanche Energy	Single Pulse, V_{DD} = 15 V, I_D=13.5A		54	205	mJ
I_{AR}	Drain-Source Avalanche Current				13.5	A
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C		29		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			500	µA
I_{GSS}	Gate–Body Leakage	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 1 mA	1	1.4	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C		–3		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 10 V, I_D = 12.5 A V_{GS} = 4.5 V, I_D = 10 A V_{GS}= 10 V, I_D = 12.5A, T_J= 125°C		8.6 10.3 12.5	10.5 13.0 16.0	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = 10 V, V_{DS} = 5 V	50			A
g_{FS}	Forward Transconductance	V_{DS} = 15 V, I_D = 12.5 A		44		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz		1200		pF
C_{oss}	Output Capacitance			350		pF
C_{rss}	Reverse Transfer Capacitance			120		pF
R_G	Gate Resistance	V_{GS} = 15 mV, f = 1.0 MHz		1.6		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 15 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		10	20	ns
t_r	Turn–On Rise Time			6	12	ns
$t_{d(off)}$	Turn–Off Delay Time			28	45	ns
t_f	Turn–Off Fall Time			12	22	ns
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 15 V, I_D = 1 A, V_{GS} = 4.5 V, R_{GEN} = 6 Ω		14	25	ns
t_r	Turn–On Rise Time			13	23	ns
$t_{d(off)}$	Turn–Off Delay Time			20	32	ns
t_f	Turn–Off Fall Time			11	20	ns
$Q_{g(TOT)}$	Total Gate Charge at Vgs=10V	V_{DD} = 15 V, I_D = 12.5 A		21	29	nC
Q_g	Total Gate Charge at Vgs=5V			11	15	nC
Q_{gs}	Gate–Source Charge			3		nC
Q_{gd}	Gate–Drain Charge			4		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				4.4	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 4.4 A (Note 2) V_{GS} = 0 V, I_S = 7 A (Note 2)		0.5 0.6	0.7	V
t_{rr}	Diode Reverse Recovery Time	I_F = 12.5A, d_{iF}/d_t = 300 A/µs (Note 3)		17		nS
Q_{rr}	Diode Reverse Recovery Charge			11		nC

Electrical Characteristics

T_A = 25°C unless otherwise noted

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) $R_{\theta JA}$ = 40°C/W when mounted on a 1in^2 pad of 2 oz copper

b) $R_{\theta JA}$ = 96°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

3. Maximum current is calculated as: $\sqrt{\frac{P_D}{R_{DS(ON)}}}$

where P_D is maximum power dissipation at T_C = 25°C and $R_{DS(on)}$ is at $T_{J(max)}$ and V_{GS} = 10V. Package current limitation is 21A

Typical Characteristics

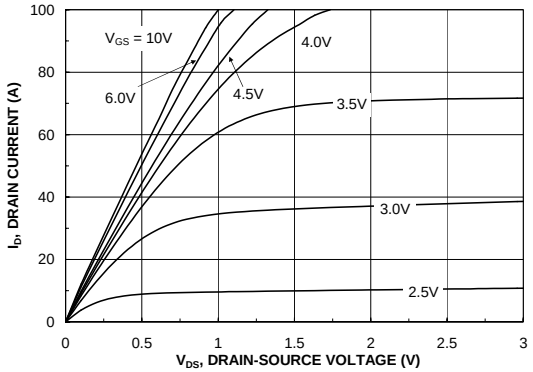


Figure 1. On-Region Characteristics.

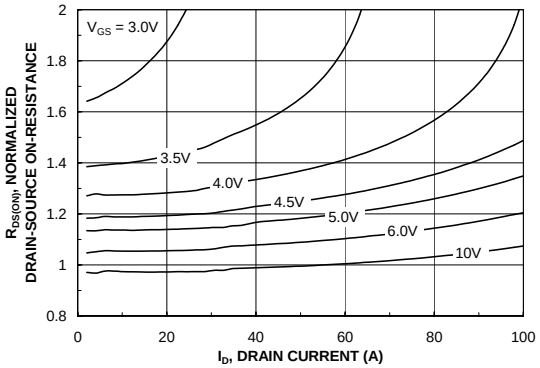


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

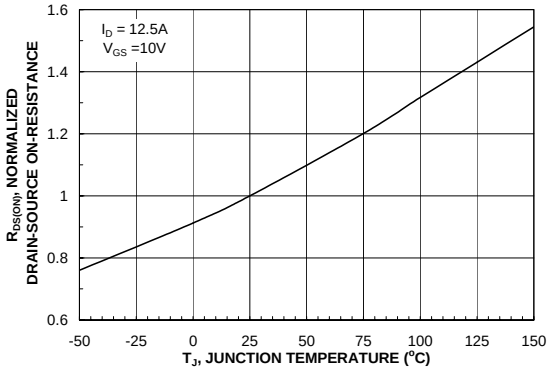


Figure 3. On-Resistance Variation with Temperature.

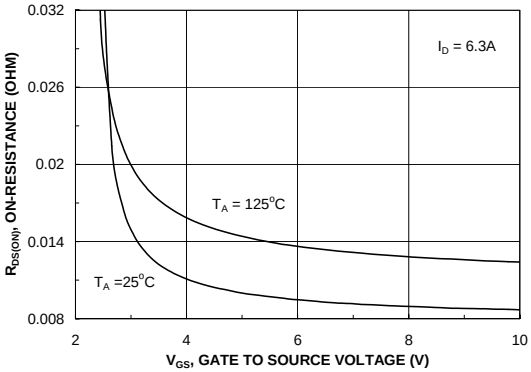


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

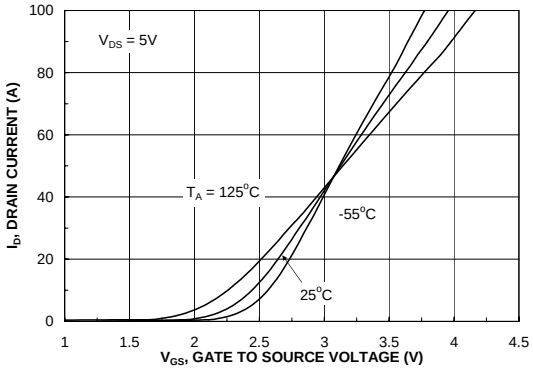


Figure 5. Transfer Characteristics.

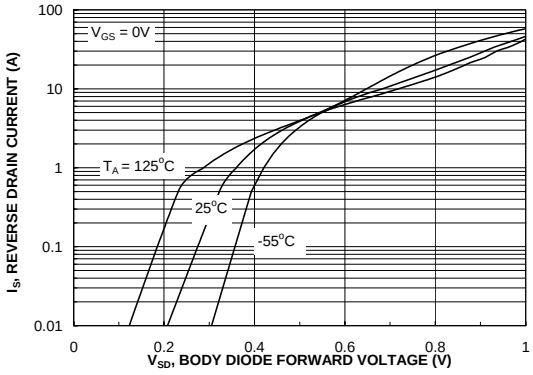


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

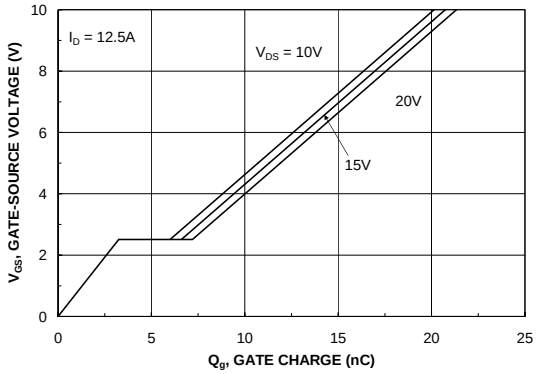


Figure 7. Gate Charge Characteristics.

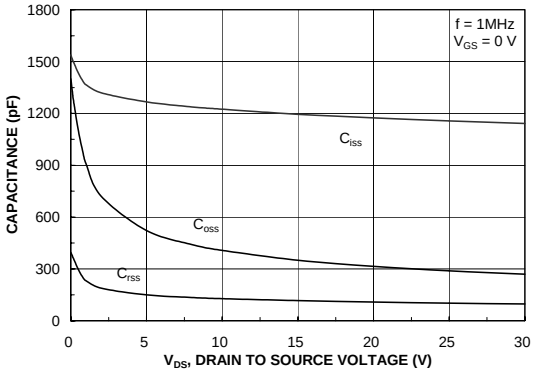


Figure 8. Capacitance Characteristics.

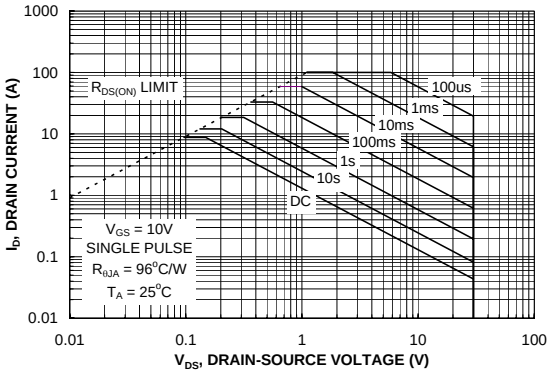


Figure 9. Maximum Safe Operating Area.

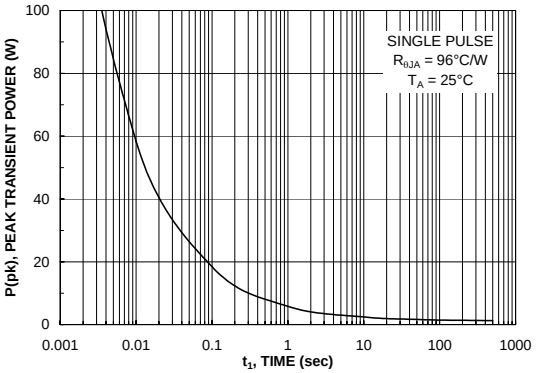


Figure 10. Single Pulse Maximum Power Dissipation.

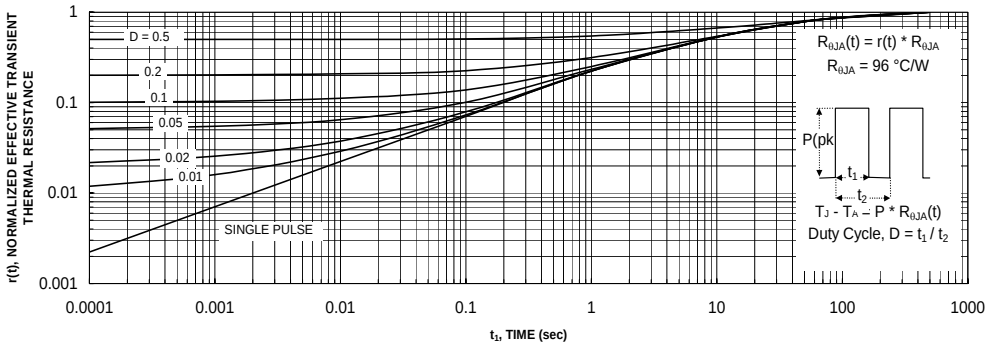


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDD6680AS.

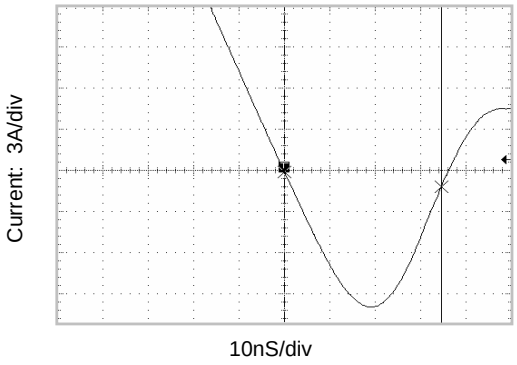


Figure 12. FDD6680AS SyncFET body diode reverse recovery characteris

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDD6680).

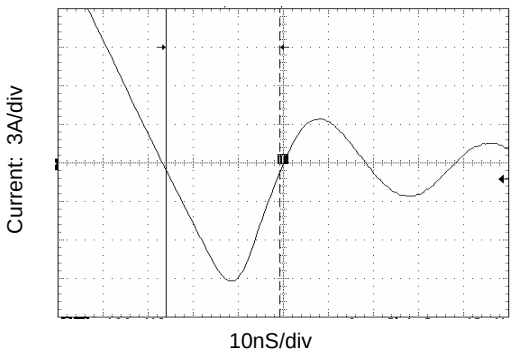


Figure 13. Non-SyncFET (FDD6680) body diode reverse recovery characteristic.

Schottky barrie diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

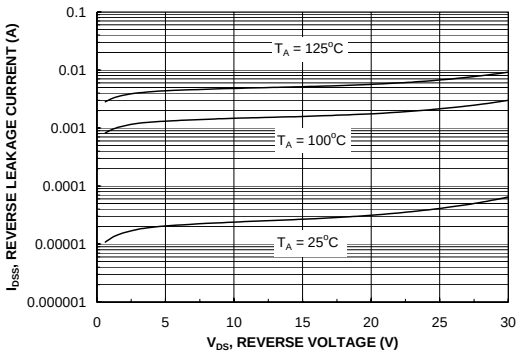


Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature.

Typical Characteristics

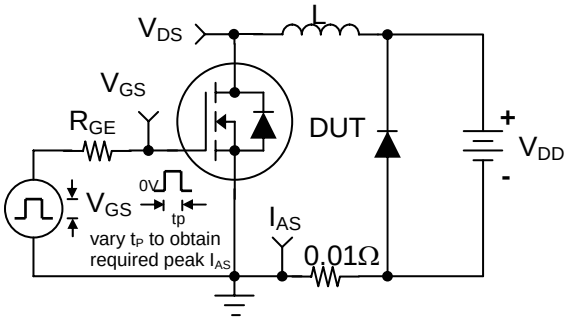


Figure 12. Unclamped Inductive Load Test Circuit

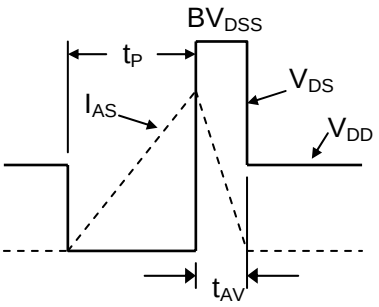


Figure 13. Unclamped Inductive Waveforms

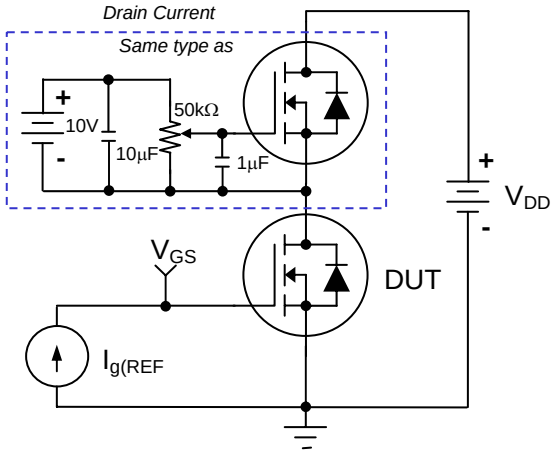


Figure 14. Gate Charge Test Circuit

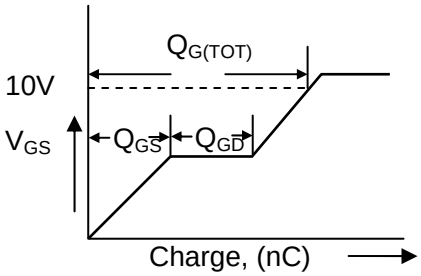


Figure 15. Gate Charge Waveform

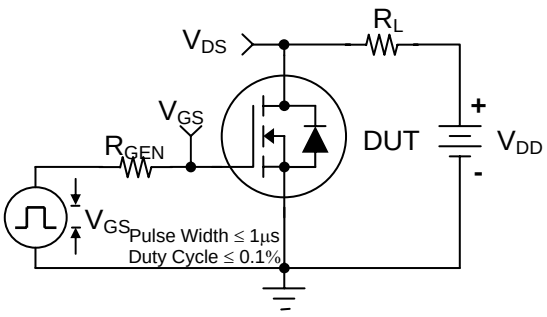


Figure 16. Switching Time Test Circuit

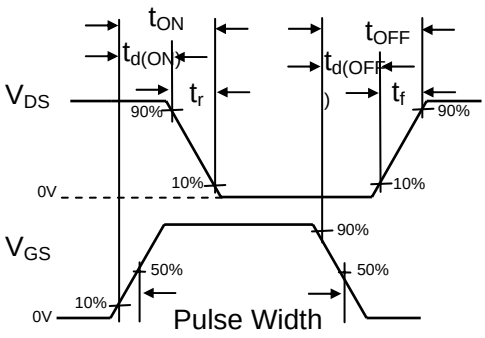
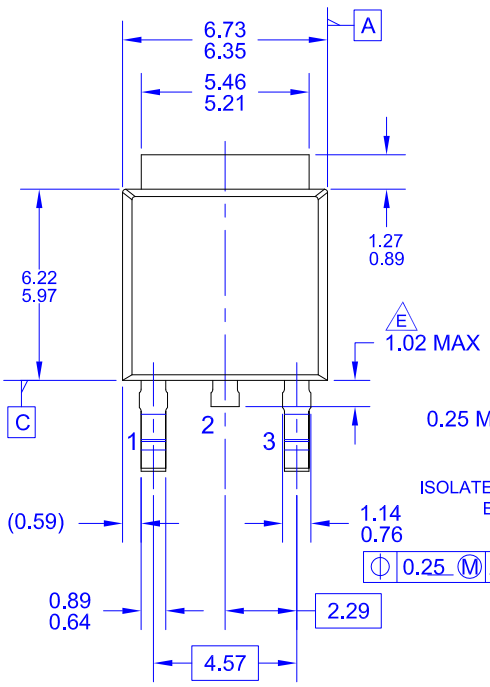
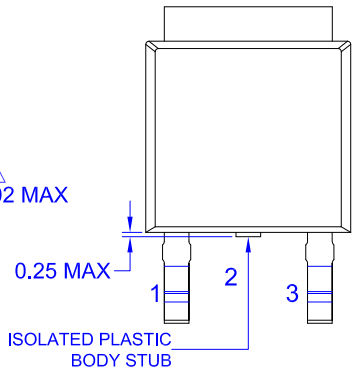


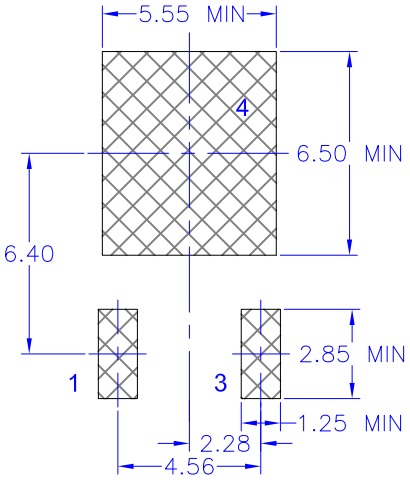
Figure 17. Switching Time Waveforms



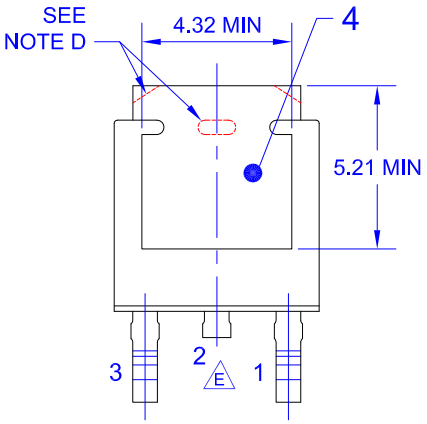
NON-DIODE PRODUCTS VERSION



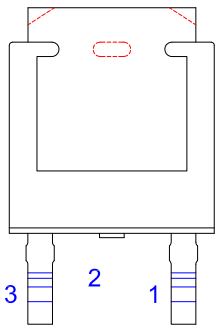
DIODE PRODUCTS VERSION



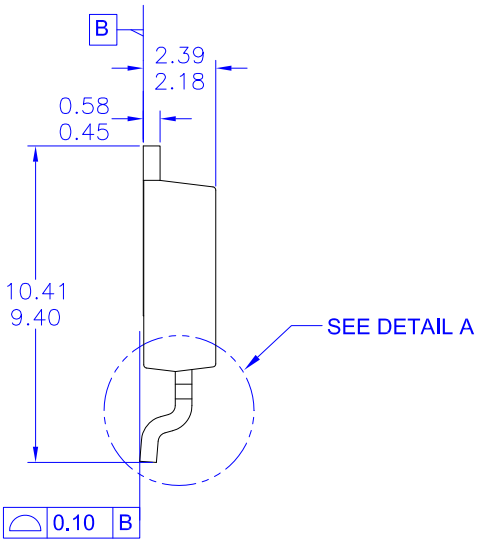
LAND PATTERN RECOMMENDATION



NON-DIODE PRODUCTS VERSION

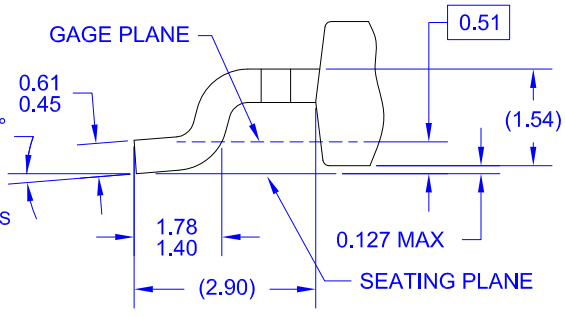


DIODE PRODUCTS VERSION



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



DETAIL A
(ROTATED -90°)
SCALE: 12X

FAIRCHILD

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative